

U.S. Department of Commerce, Patent and Trademark Office				Atty Docket No.		Serial No.		
				M-10095 US		09/661,328		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Applicant(s)				
(Use several sheets if necessary)				Zhang et al.				
				Filing Date		Group		
				September 14, 2001		2812		
U.S. Patent Documents								
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OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)								
HR	AQ	X. Jin, "An Effective Gate resistance Model for CMOS RF and Noise Modeling", Digest of Technical Papers IEDM-98, December 1998, pages 961-9694.						
HR	AR	S.F. Tin et al., "A Simple Subcircuit Extension of the BSIM3V3 Model of CMOS RF Design," IEEE Journal of Solid-State Circuits, Vol. 35, No. 4, April 2000, pp. 612-623.						
HR	AS	W. Liu et al., "RF MOSFET Modeling Accounting for Distributed Substrate and Channel Resistance with Emphasis on BSIM3V3 SPICE Model", Digest of Technical Papers IEDM-97, December 1997, pages 309-312.						
Examiner		Date Considered 03/25/2004						
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HR	AQ	S.H. Jen et al., "Accurate Modeling and Parameter Extraction of MOS Transistors up to 10 GHz," IEEE Transactions on Electronic Devices, Vol. 46, No. 11, November 1999, pp. 2217-2227.						
HR	AR	C. Enz et al., "MOS Transistor Modeling for RF IC Design," IEEE Transactions on Solid-State Circuit, Vol. 35, No. 2, February 2000, pp. 186-2001						
HR	AS	M.E. Mokari et al., "A New Method of Noise Parameter Calculation Using Direct Matrix Analysis," IEEE Transactions on Circuits and Systems-1: Fundamental Theory and Applications, Vol. 39, No. 9, September 1992, pp. 767-771.						
Examiner		Helen Lopez		Date Considered 03/25/2004				
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He	AQ	T.E. Kolding, "Test Structure for Universal Estimation of MOSFET Substrate Effects at Gigahertz Frequencies," IEEE International Conference on Microelectronic Test Structures, March 2000, pp. 106-111.							
He	AR	C.C. Su et al., "A Monolithic 2.4 GHz CMOS Active Balanced Circuit," IEEE, Vol. 2, November 1999, pp. 214-217.							
He	AS	K. H. Kim et al., "Full Software Analysis and Impedance Matching of Radio Frequency CMOS Integrated Circuits," IEEE Transactions on Components and Packaging Technologies, Vol. 23, No. 1, March 2000, pp. 183-189.							
Examiner		Julia Rosenthal		Date Considered 03/25/2004					
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HR	AQ	Hi-Deok Lee et al., "Characterization of Crosstalk-Induced Noise for 0.18 μ m CMOS Technology with 6-Level Metalization Using Time Domain Reflectometry and S. Parameters," IEEE: International Electronic Devices Meeting, December 5, 1999, pp. 37.4.1-37.4.4.							
HR	AR	J. J. Ou et al., "Submicron CMOS Thermal Noise Modeling from an RF Perspective," IEEE Symposium on VLSI Technology Digest of Technical Papers, 1999, pp151-152.							
HR	AS	J. Zheng et al., "CAD-Oriented Equivalent Circuit Modeling of On-Chip Interconnects for RF Integrated Circuits in CMOS Technology," IEE MTT-S International Microwave Symposium Digest, June, 1999, Vol. 1, pp. 35-38.							
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HR	AQ	Behzad Razavi, "CMOS Technology Characterization for Analog and RF Design," IEEE Journal of Solid-State Circuits, Vol. 34, No. 3, pp.268-276.							
HR	AR	Behzad Razavi, "CMOS Technology Characterization for Analog and RF Design," IEEE Custom Integrated Circuits Conference, 1998, pp. 3.1.1-3.1.8.							
HR	AS	W.S. Kwan et al., "Hot-Carrier Effects on the Scattering of Lightly Doped Drain N-Type Metal-Oxide-Semiconductor Field Effects Transistors," Journal of Vacuum Science and Technology B: Micro Electronics and Nanometer Structures, Vol. 16, No. 2, pp. 628-632.							
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Hela Rohatshib		03/25/2004							
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<i>HR</i>	AQ	C. E. Biber et al., "Improvements on a MOSFET Model for Non-Linear RF Simulations," 1997 IEEE MTT-S International Microwave Symposium Digest, June, 1997, Vol. 2, pp. 865-868.							
<i>HR</i>	AR	Jin-Young Choi et al., "Effects of Substrate Resistance on Microwave Characteristics of MOS Transistors," Journal of Electrical Engineering and Information Science, 1999, Volume 4, No. 2, pp. 244-248.							
<i>HR</i>	AS	Jin-Young Choi, "Macro Modeling of MOS Transistors for RF Applications," Journal of the Institute of Electronics Engineers of Korea, 1999, Vol. 36-D, No. 5, pp. 54-62.							
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HE	AQ	Weidong Liu et al., "PSIM4.0.0 MOSFET Model-User's Manual," UC Berkeley-Department of Electrical Engineering and Computer Sciences, 2000, pp. 1.1-13.14.						
HE	AR	Hewlett-Packard Application Note 57-1, "Fundamentals of RF and Microwave Noise Figure Measurements," pp. 1-40.						
HE	AS	Lawrence T. Pillage et al., "Simulation of Nonlinear Circuits," <u>Electronic Circuit and System Simulation Methods</u> , 1994, Chapter 10, pp. 285-314.						
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